









CEP25A04

40V Δ 1.8mΩ Δ 200A Δ Si MOSFET

SILICON Si MOSFET ▲ THT type
N-channel enhancement mode
UL94V-0 rated flame retardant epoxy
TO220-3L package

Super high dense cell density for extremely low R_{DS(ON)} **High power and current handling capability**

MAXIMUM RATINGS

Parameter (T_c = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V _{DS}	40V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at T _C = 25°C	I _D	200A
Continuous Drain Current at T _C = 100°C	I _D	126A
Pulsed Drain Current Note 1	I _{DM}	800A
Maximum Power Dissipation at T _C = 25°C	P _D	166W
Power Dissipation Derating above 25°C	ΔP_D	1.32W/°C
Single Pulsed Avalanche Energy Note 4	E _{AS}	760mJ
Single Pulsed Avalanche Current Note 4	l _{AS}	39A
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

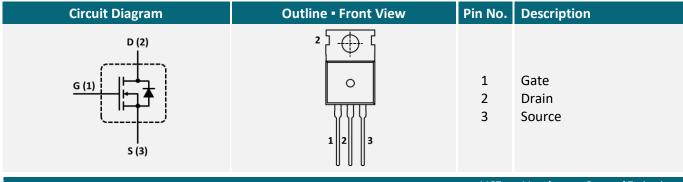
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	0.75°C/W
Thermal Resistance, Junction-to-Ambient	R _{TH JA}	62.5°C/W

APPLICATIONS

Battery Management Systems	DC/DC	High Side	Industrial	Low Side
	Converter	Switches	Control	Switches
+4-				

PIN DESCRIPTION



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ELECTRICAL CHARACTERISTICS ▲ T_C = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 250\mu A$	BV_{DSS}	40			V
Zero Gate Voltage Drain Current	$V_{DS} = 40V$, $V_{GS} = 0V$	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V$, $V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I_{GSSR}			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_{D} = 250 \mu A$	$V_{GS(th)}$	2		4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 30A$	R _{DS(ON)}		1.8	2.3	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 9V$, $I_{D} = 30A$	R _{DS(ON)}		1.9	2.5	mΩ
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		6120		pF
Output Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		1715		pF
Reverse Transfer Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, $f = 1MHz$	C_{RSS}		1330		pF
Switching Characteristics Note 3						
Turn-On Delay Time	V_{DD} = 15V, V_{GS} = 10V, I_{D} = 15A, $R_{G(ext)}$ = 1 Ω	t _{D(ON)}		44		ns
Turn-On Rise Time	V_{DD} = 15V, V_{GS} = 10V, I_{D} = 15A, $R_{G(ext)}$ = 1 Ω	t_{R}		35		ns
Turn-Off Delay Time	V_{DD} = 15V, V_{GS} = 10V, I_D = 15A, $R_{G(ext)}$ = 1 Ω	t _{D(OFF)}		79		ns
Turn-Off Fall Time	V_{DD} = 15V, V_{GS} = 10V, I_D = 15A, $R_{G(ext)}$ = 1 Ω	t _F		33		ns
Total Gate Charge	$V_{DS} = 15V$, $V_{GS} = 10V$, $I_D = 50A$	Q_{G}		235		nC
Gate Source Charge	$V_{DS} = 15V$, $V_{GS} = 10V$, $I_D = 50A$	Q_{GS}		47		nC
Gate Drain Charge	$V_{DS} = 15V$, $V_{GS} = 10V$, $I_D = 50A$	Q_{GD}		88		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current		Is			138	А
Drain-Source Diode Forward Voltage Note 2	V _{GS} = 0V, I _S = 30A	V_{SD}			1.2	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: L = 1mH, $I_{AS} = 39A$, $V_{DD} = 24V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$.



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

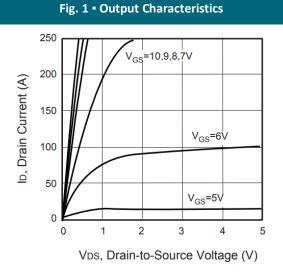
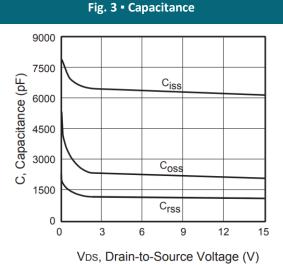
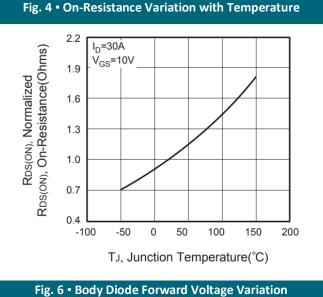
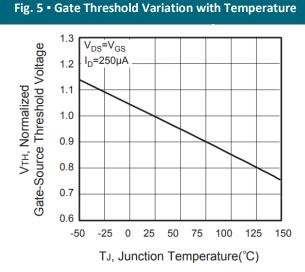


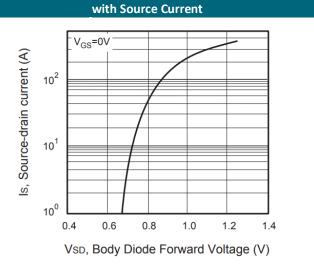
Fig. 2 • Transfer Characteristics

300
(V) 240
180
120
25°C
0
2 4 6 8 10
Ves, Gate-to-Source Voltage (V)









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REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

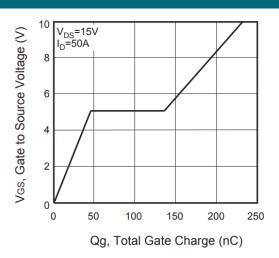


Fig. 8 • Maximum Safe Operating Area

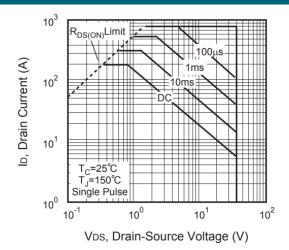
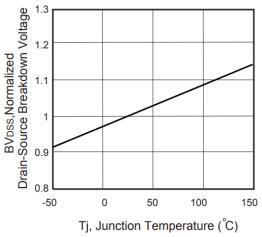


Fig. 9 • Breakdown Voltage Variation vs. Temperature



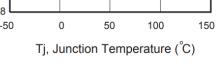


Fig. 10 • Switching Test Circuit

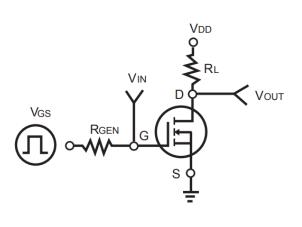
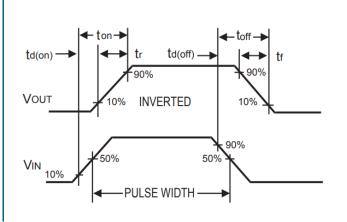


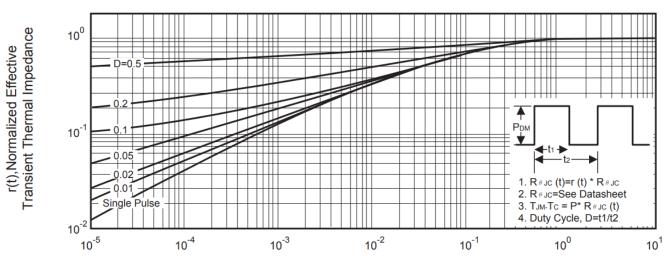
Fig. 11 • Switching Waveforms





REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

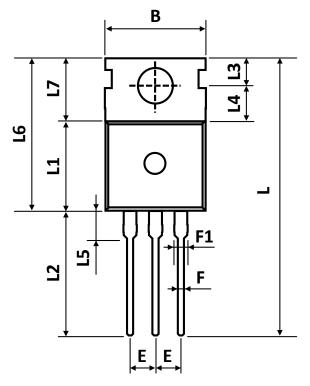
Fig. 12 • Normalized Thermal Transient Impedance Curve

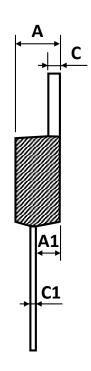


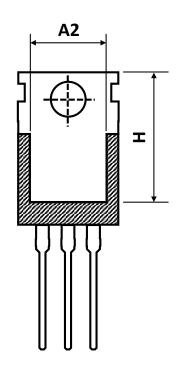
Square Wave Pulse Duration (sec)



PACKAGE OUTLINE







Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	4.43	4.53	4.63
A1	2.30	2.40	2.50
A2	7.70	7.90	8.10
В	9.80	10.00	10.20
С	1.25	1.30	1.40
C1	0.45	0.50	0.60
D	3.45	3.60	3.70
E	2.45	2.54	2.60
F	0.70	0.80	0.95
F1	1.15	1.33	1.50
L	26.80	28.80	30.80
L1	9.20	9.30	9.40
L2	12.80	13.10	13.40
L3	2.70	2.80	2.90
L4	3.50	3.70	3.80
L5	2.60	2.90	3.20
L6	15.40	15.80	16.20
L7	6.20	6.50	6.80
Н	12.95	13.25	13.55

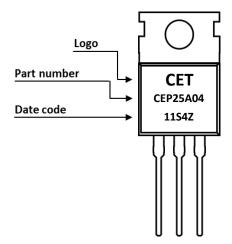
ORDERING INFORMATION

Part Number	Package	Packing	Tube Qty.	Inner Box Qty.	Outer Box Qty.
CEP25A04	TO-220-3L	Tube	50pcs	1,000pcs	4,000pcs

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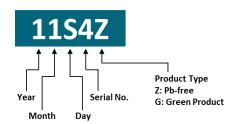


PART MARKING



DATE CODE

Example: 11S4Z



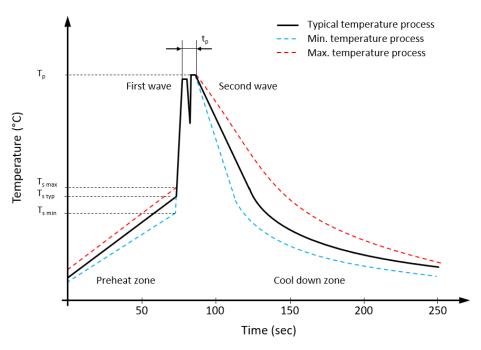


Coding list for "Day"





RECOMMENDED WAVE SOLDERING PROFILE A THT PACKAGE



Classification wave soldering profile ▲ Refer to EN 61760-1: 2006

Profile Features		Value ▲ Sn-Pb Assembly	Value ▲ Pb-free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	100 °C
Preheat temperature typical	T _{s typ}	120 °C	120 °C
Preheat temperature max.	T _{s max}	130 °C	130 °C
Preheat time t_s from T_{smin} to T_{smax}	ts	70 seconds	70 seconds
Peak temperature	Tp	235 °C to 260 °C	245 °C to 260 °C
Time of actual peak temperature	t _p	Max. 10 seconds Max. 5 second each wave	Max. 10 seconds Max. 5 second each wave
Ramp-down date min.		~ 2 °C/second	~ 2 °C/second
Ramp-down rate typical		~ 3.5 °C/second	~ 3.5 °C/second
Ramp-down rate max.		~ 5 °C/second	~ 5 °C/second
Time 25°C to 25°C		4 minutes	4 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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